TOSHIBA MP4304

TOSHIBA POWER TRANSISTOR MODULE SILICON NPN EPITAXIAL TYPE (HIGH GAIN POWER TRANSISTOR 4 IN 1)

MP4304

HIGH POWER SWITCHING APPLICATIONS.

HAMMER DRIVE, PULSE MOTOR DRIVE AND INDUCTIVE LOAD SWITCHING.

- Small Package by Full Molding (SIP 12 Pin)
- High Collector Power Dissipation (4 Devices Operation)

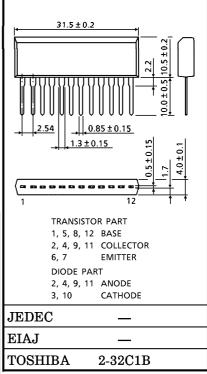
 $: P_T = 4.4W (Ta = 25^{\circ}C)$

- High Collector Current: IC (DC)=3A (Max.)
- High DC Current Gain: $h_{FE} = 600$ (Min.) ($V_{CE} = 2V$, $I_{C} = 1A$)

MAXIMUM RATINGS (Ta = 25°C)

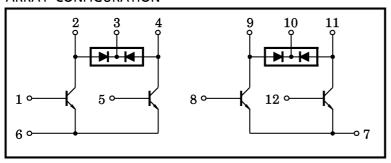
CHARACTERI	SYMBOL	RATING	UNIT		
Collector-Base Voltage	v_{CBO}	80	V		
Collector-Emitter Volta	v_{CEO}	80	V		
Emitter-Base Voltage	v_{EBO}	7	V		
Collector Current	DC	$I_{\mathbb{C}}$	3	A	
Conector Current	Pulse	ICP	5	A	
Continuous Base Curre	$I_{\mathbf{B}}$	0.5	A		
Collector Power Dissipation (1 Device Operation)		PC	2.2	W	
Collector Power Dissipa (4 Devices Operation)	PT	4.4	W		
Junction Temperature	T_{j}	150	°C		
Storage Temperature R	$T_{ m stg}$	T _{stg} -55~150			

INDUSTRIAL APPLICATIONS Unit in mm



Weight: 3.9g

ARRAY CONFIGURATION



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TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.

In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..

The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance of Junction to Ambient (4 Devices Operation, Ta=25°C)	$\Sigma R_{ ext{th (j-a)}}$	28.4	°C/W
Maximum Lead Temperature for Soldering Purposes (3.2mm from Case for 10s)	$\mathrm{T_{L}}$	260	$^{\circ}\mathrm{C}$

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHAR	ACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 80V, I_{E} = 0$	_	_	10	μ A
Emitter Cu	t-off Current	I_{EBO}	$V_{EB} = 7V, I_{C} = 0$	_	_	10	μ A
Collector-Ba Breakdown		V (BR) CBO	$I_{\rm C}=1{ m mA},~I_{\rm E}=0$	80	_	_	V
Collector-En Breakdown		V (BR) CEO	$I_{C}=10mA, I_{B}=0$	80	_	_	V
DC Current Gain		h _{FE} (1)	$V_{CE}=2V$, $I_{C}=1A$	600	_	_	
DC Current	DC Current Gain		$V_{CE}=2V$, $I_{C}=2A$	150	_	_	
Saturation Voltage	Collector-Emitter	V _{CE} (sat)	$I_{C} = 1.5A, I_{B} = 15mA$	_	0.25	0.5	V
	Base-Emitter	V _{BE (sat)}	$I_{C} = 1.5A, I_{B} = 15mA$	_	_	1.2	
Transition Frequency		$f_{ m T}$	$V_{CE} = 2V, I_{C} = 0.1A$	_	85	_	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		50	_	pF
Switching Time	Turn-on Time	ton	$\begin{array}{c c} 20\mu s & I_{B1} & OUTPUT \\ \hline INPUT & \hline M & I_{B2} \\ \hline I_{B1} & I_{B2} \\ \hline \\ V_{CC} = 30V \\ \end{array}$	_	0.4	_	
	Storage Time	t_{stg}		_	2.6	_	μs
	Fall Time	tf	$V_{CC}=30V$ $I_{B1}=-I_{B2}=15$ mA, $DUTY\ CYCLE \le 1\%$	_	1.3	_	

FLYBACK-DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Maximum Forward Current	$I_{ extbf{FM}}$		_	_	3	Α
Reverse Current	$I_{\mathbf{R}}$	$V_R = 80V$	_	_	0.4	μ A
Reverse Voltage	$v_{ m R}$	$I_R = 100 \mu A$	80	_	_	V
Forward Voltage	$ m V_{f F}$	$I_{\mathbf{F}} = 1\mathbf{A}$		_	1.5	V

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